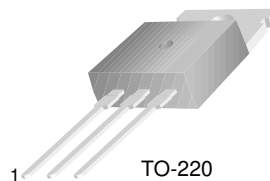


KSD362

B/W TV Horizontal Deflection Output

- Collector-Base Voltage : $V_{CBO}=150V$
- Collector Current : $I_C=5A$
- Collector Dissipation : $P_C=40W(T_C=25^\circ C)$



TO-220
1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current	5	A
P_C	Collector Dissipation ($T_C=25^\circ C$)	40	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ C$

Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1mA, I_E = 0$	150			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 2mA, R_{BE} = \infty$	70			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1mA, I_C = 0$	8			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 100V, I_E = 0$			20	μA
h_{FE}	DC Current Gain	$V_{CE} = 5V, I_C = 5A$	20		140	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5A, I_B = 0.5A$			1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 5A, I_B = 0.5A$			1.5	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 5V, I_C = 0.5A$		10		MHz

h_{FE} Classification

Classification	N	R	O
h_{FE}	20 ~ 50	40 ~ 80	70 ~ 140

Typical Characteristics

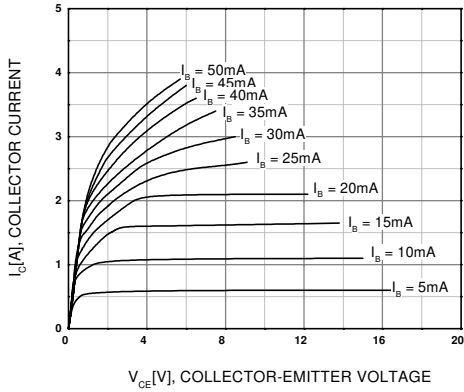


Figure 1. Static Characteristic

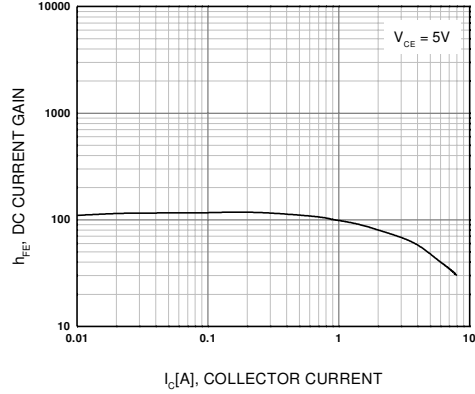


Figure 2. DC current Gain

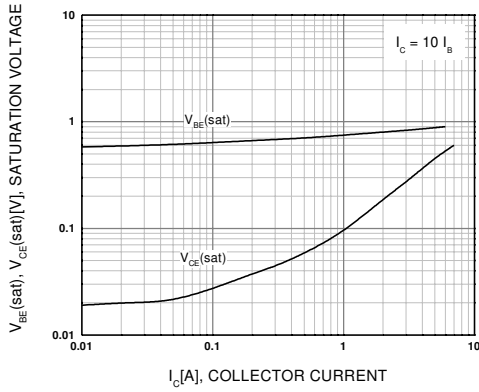


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

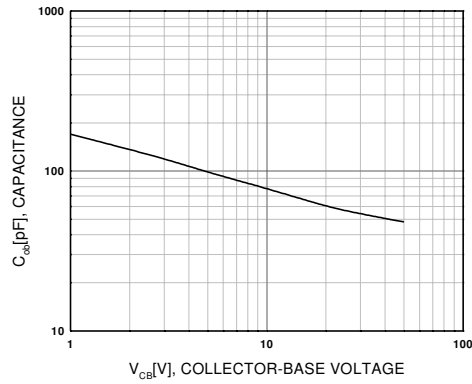


Figure 4. Collector Output Capacitance

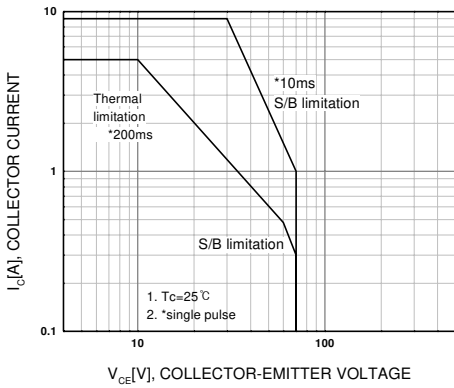


Figure 5. Safe Operating Area

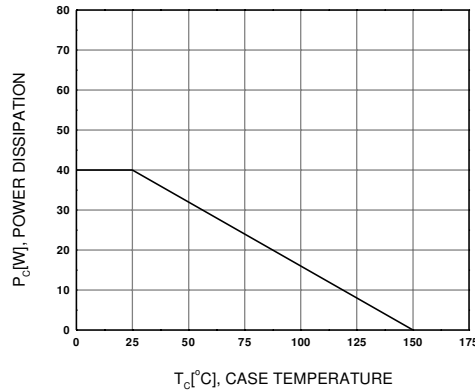
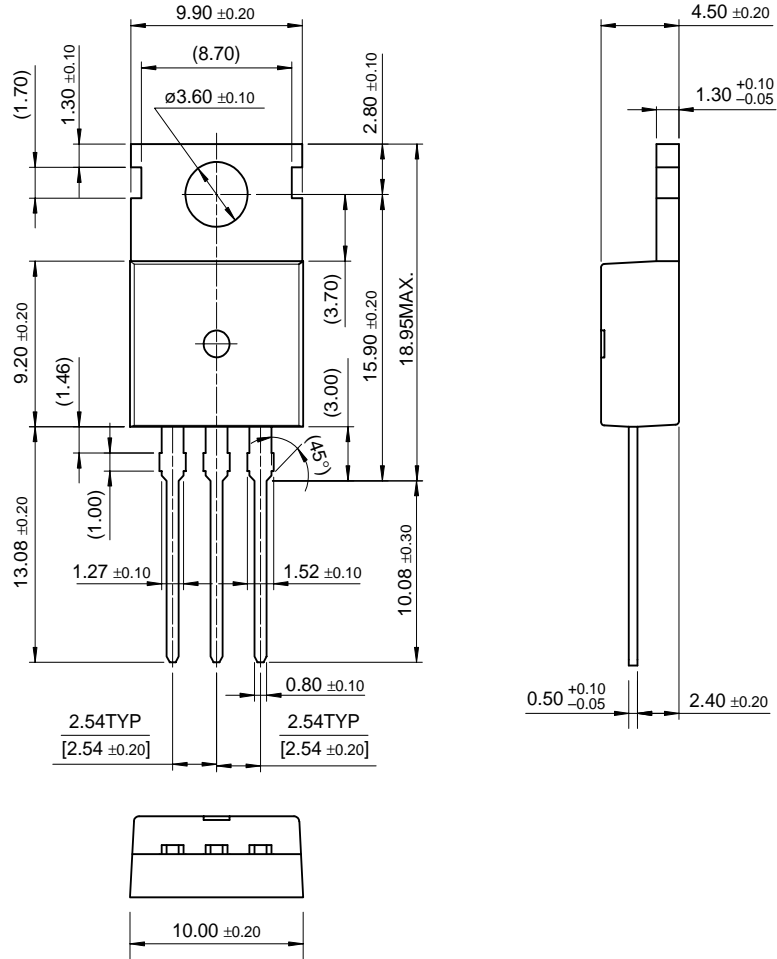


Figure 6. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

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KSD362
NPN Epitaxial Silicon Transistor

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Features

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Applications

B/W TV Horizontal Deflection Output

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSD362RTU	Full Production	\$0.353	TO-220	3	RAIL
KSD362N	Full Production	\$0.353	TO-220	3	BULK
KSD362R	Full Production	\$0.353	TO-220	3	BULK

* 1,000 piece Budgetary Pricing

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